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(54) Title: LOW- κ BORON CARBONITRIDE FILMS

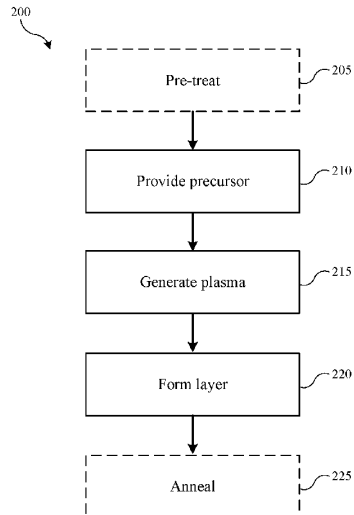


FIG. 2

(57) Abstract: Exemplary methods of semiconductor processing may include providing a boron-and-carbon-and-nitrogen-containing precursor to a processing region of a semiconductor processing chamber. A substrate may be disposed within the processing region of the semiconductor processing chamber. The methods may include generating a capacitively-coupled plasma of the boron-and-carbon-and-nitrogen-containing precursor. The methods may include forming a boron-and-carbon-and-nitrogen-containing layer on the substrate. The boron-and-carbon-and-nitrogen-containing layer may be characterized by a dielectric constant below or about 3.5.

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